

$$20 \log_{10} |A_v| = A_{v \text{ dB}}$$

$$20 \log_{10} |A_f| = A_{f \text{ dB}}$$

$$10 \log_{10} A_p = A_{p \text{ dB}}$$

$$\log_{10} (1) = 0$$

$$\log_{10} (10) = 1$$

$$\log_{10} (10^x) = x$$

$$\log_{10} (2) = 0.3$$

$$\log (a.b) = \log a + \log b$$

A_p A_v or A_f	$A_{v \text{ dB}}$ or $A_{f \text{ dB}} = 20 \log_{10} A_v$ or $20 \log_{10} A_f$	$A_{p \text{ dB}} = 10 \log_{10} A_p$
$1/\sqrt{2} = 0.707$	-3	-1.5
$\sqrt{2} = 1.414$	+3	+1.5
2	+6	+3
4 = 2^2	12	6
10	20	10
20	26	13
100 = 10^2	40	20
200	46	26
1000 = 10^3	60	30
10 000 = 10^4	80	40
100 000 = 10^5	100	50

NOTE

When dB values are given Ratio values can be obtained as follows.

$$A_{v \text{ dB}} = 20 \log_{10} A_v \Rightarrow A_v = 10^{A_{v \text{ dB}}/20}$$

$$A_{f \text{ dB}} = 20 \log_{10} A_f \Rightarrow A_f = 10^{A_{f \text{ dB}}/20}$$

$$A_{p \text{ dB}} = 10 \log_{10} A_p \Rightarrow A_p = 10^{A_{p \text{ dB}}/10}$$

Ex. 1/ If $A_{v,dB} = 83 \text{ dB} = 80 \text{ dB} + 3 \text{ dB}$
 then $A_v = 10^{(83/20)} = 10^4 \times 1.414 = 14140 //$

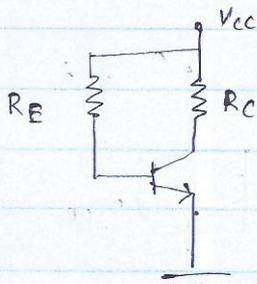
2/ If $A_{p,dB} = 33 \text{ dB} = 30 \text{ dB} + 3 \text{ dB}$
 $A_p = 10^{(33/10)} = 10^{3.3} = 10^3 \times 2 = 2000 //$

BJT Amp. Circuits

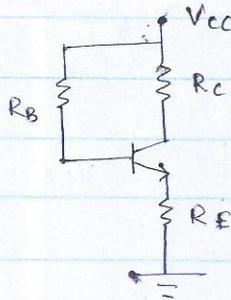
chapter 5

BJT AC Analysis.

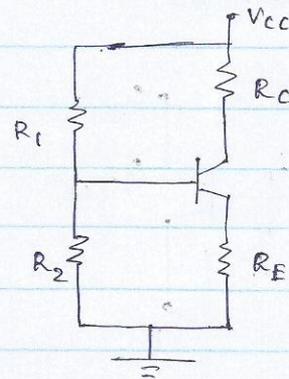
Note: BJT DC Analysis (Biasing circuits) } covered in Sem III Electronics I



① Fixed Bias cct.



② Fixed Bias cct. with emitter res.



③ Potential Divider Biasing cct.

* Best Biasing cct → ③

* Worst " " → ①

BJT AC Models (Equivalent ccts.)

(1). re model (simplified model). (2 parameter model) ⇒ $r_e, \beta(\alpha)$

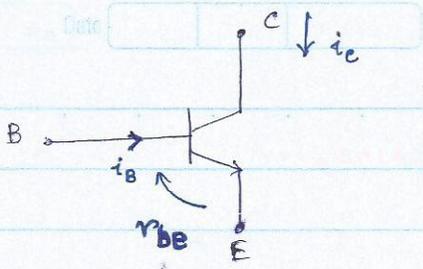
(2). Hybrid model.

→ hybrid parameter (h-parameter) model (4 parameter model) ⇒ h_i, h_f, h_r, h_o

→ hybrid- π model (much more than 4 para.)

used for high freq. analysis & design

For low to mid freq. Range

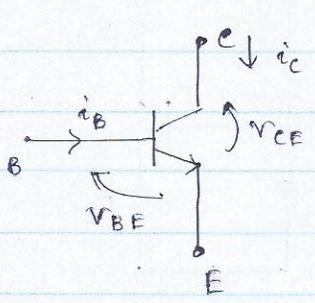


- V_{BE} = DC BE voltage
- v_{be} = AC instantaneous BE Vol.
- V_{BE} = Total BE Vol.
- V_{be} = RMS BE Vol. (of the ac quantities)
- V_{bep} or V_{bem} = Peak or Maximum BE Voltage (ac quantity)

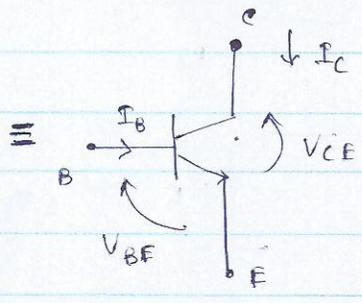
In a BJT amp. cct.

$$V_{BE}(t) = V_{BE} + v_{be}(t)$$

Total BE voltage (instantaneous value)
DC BE voltage (DC bias voltage)
instantaneous ac vol.



Total (DC+AC)

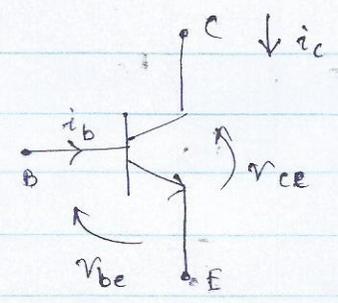


DC

DC Analysis to find Q point.

(I_B, I_C, V_{BE}, V_{CE})

(DC Models) or Load lines (DLL)



AC

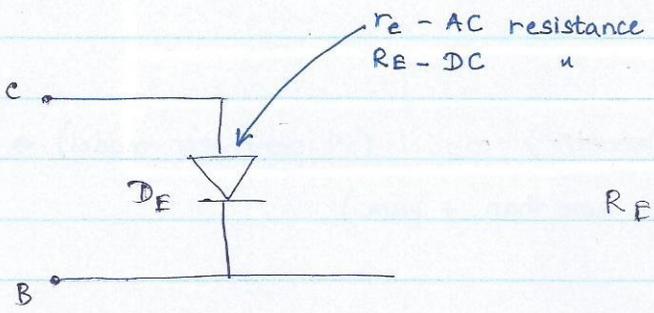
AC Analysis to find gains/amplifications, I/P, O/P, Imp, BW.

AC Models or

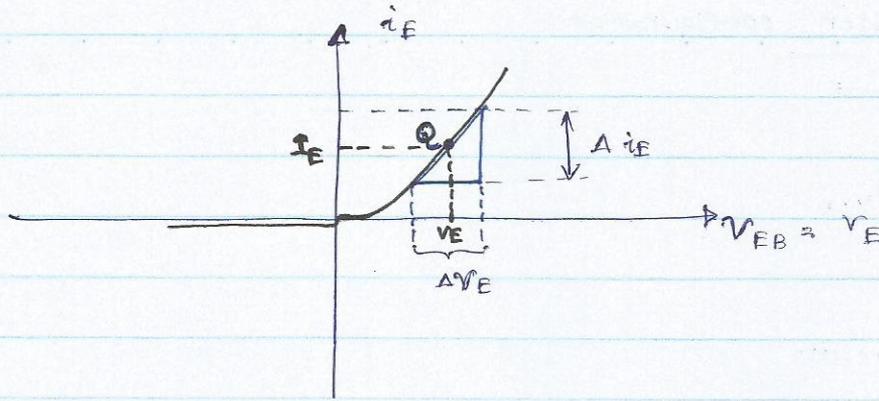
Load lines (ACLL)

r_e model
h-para model

r_e model



$$R_E = \frac{V_E}{I_E}$$



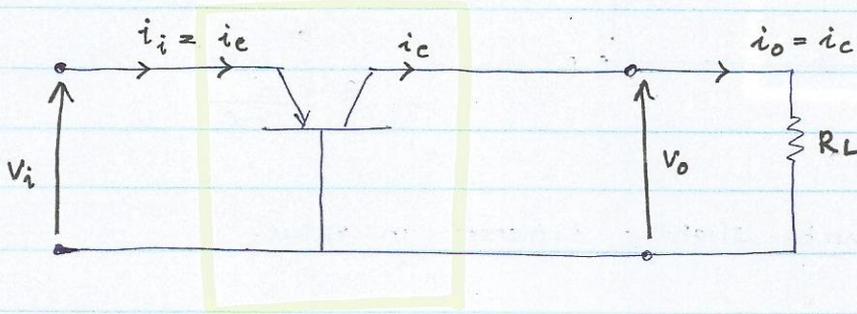
$$R_E = \frac{V_E}{I_E}$$

$$r_e = \frac{\Delta V_E}{\Delta i_E}$$

NOTE: From diode lecture (ET 2001)

$$r_e \approx \frac{V_T}{I_E} = \frac{26 \text{ mV}}{I_E} \quad \text{at room temp. } 27^\circ\text{C} \approx 300\text{K}$$

Common Base Configuration



$$A_V = \frac{v_o}{v_i}$$

$$v_o = i_o R_L = i_c R_L$$

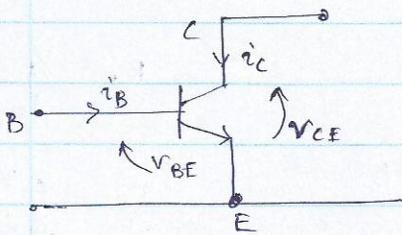
$$i_c = \alpha i_e$$

$$v_o = \alpha i_e R_L$$

$$v_i = i_e r_e$$

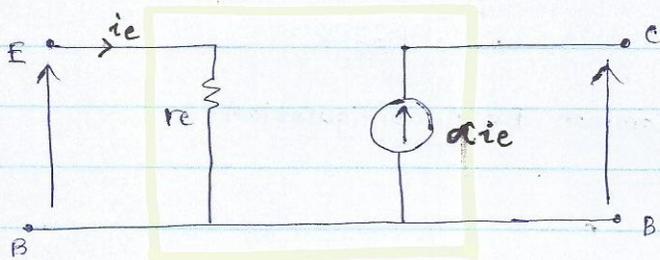
$$A_V = \frac{\alpha R_L}{r_e}$$

Common Emitter configuration.



Total circuit

r_e model for Common Base.



$$\alpha = \frac{\beta}{\beta + 1}$$

or

$$\beta = \frac{\alpha}{1 - \alpha}$$

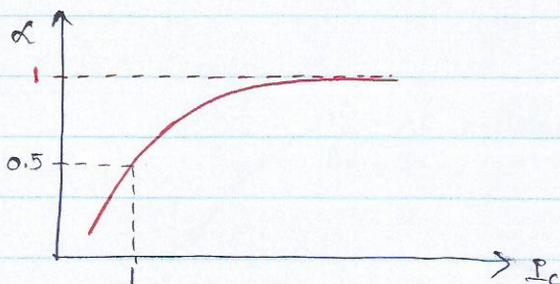
① Note → α_{dc} and α_{ac} can be slightly different in value.

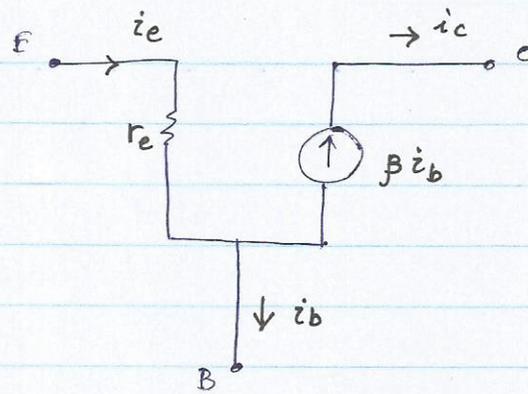
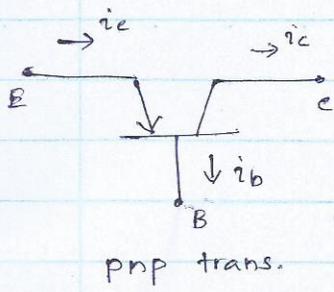
→ It is common to assume $\alpha_{dc} \approx \alpha_{ac}$ when they are not given explicitly.

∴ $\alpha_{DC} \approx \alpha_{ac} \approx \alpha$ } common symbol for α

②. Same argument is applicable for β as well.

③. Usually α varies with I_c





$$\alpha i_e \approx \beta i_b$$

Question.

Draw CE and CC Eq. ccts using r_e , β as parameters. This require redrawing the Eq. ccts with,

E as common - CE

C as common - CC

Repeat for a npn BJT.